

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14941	((non\$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4) adj dop\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)).clm.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:18
L2	15289	((non\$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4) adj dop\$4)(non-doped non adj doped not-doped non adj doped i-type i-type adj semiconductor intrinsic)).clm.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:18
L3	60535	(laser light adj emitting led light\$1emitting diode\$2).ti.	US-PGPUB; USPAT	OR	ON	2008/06/12 10:20
L4	28376	(gallium near3 nitride gan algan nitride\$1based gan)	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:21
L5	28376	(gallium near3 nitride gan algan nitride\$1based)	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:21
L6	72	2 and 3 and 4	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:21
L7	47	(((((non\$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4) adj dop\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)) same (gallium near3 nitride gan algan nitride\$1based gan)).clm.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:22
L8	9	7 and 3 and 4	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:23
L9	6	(@ad<"20030917" @rlad<"20030917") and 8	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:23
L10	17	( (itype i adj type) same (gallium near3 nitride gan algan nitride\$1based gan)).clm.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:29
L11	2	("20050148194"   "6924512").PN.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:33

L12	10	("20050148194"   "6924512")	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:39
L13	1	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4) adj dop\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)) and 12	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:41
L14	1	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)) and "7087922"	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:42
L15	1	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)) and "7087922"	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:43
L16	43	((LIANG-WEN) near2 (WU)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:44
L17	27	((RU-CHIN) near2 (TU)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:44
L18	28	((CHENG-TSANG) near2 (YU)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:44
L19	27	((TZU-CHI) near2 (WEN)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:44
L20	72	((FEN-REN) near2 (CHIEN)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:44
L21	33	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)) and (16 17 18 19 20)	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:45

L22	11	("20020179914"   "20030122147"   "20030132442"   "20030189215"   "20040155248"   "20050247952"   "6533874"   "6593597"   "6847046"   "7141830"   "7180096").PN.	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:46
L23	6	(@ad< "20030917" @rlad< "20030917") and 22	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:47
L24	4	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) and 23	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:48
L25	4	"6847046"	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:53
L26	3	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) and 25	US-PGPUB; USPAT	OR	OFF	2008/06/12 10:53
L27	8	("20060102921"   "6847046"   "7049638")	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:07
L28	51	"11266019" "5808344" "56021371"	US-PGPUB; USPAT; JPO	OR	OFF	2008/06/12 11:10
L29	6	"11266019" "5808344".pn. "56021371"	US-PGPUB; USPAT; JPO	OR	OFF	2008/06/12 11:10
L30	5	"537809".ap.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:16
L31	2	"20060231901"	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:17
L32	2	"20060231901" and non \$1polar\$5	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:20
L33	2	"20060231901" and dielectric near3 material	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:21

L34	0	"20060231901" and dielectric near3 oxide	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:22
L35	0	"20060231901" and dielectric same oxide	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:22
L36	2	"20060231901" and dielectric	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 11:23
L37	4247	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) near2 (ohmic contact)	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:25
L38	4504	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) near2 (ohmic electorde wiring contact)	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:26
L39	191	38 and 4	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:27
L40	125	(@ad< "20030917" @rlad< "20030917") and 39	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:27
L41	0	( ((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) near2 (ohmic electorde wiring contact)).clm. and Goto adj Osamu.in.	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:37

L42	483	( ((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) near2 (ohmic electorde wiring contact)).clm.	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:37
L43	30	42 and 4	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:38
L44	24	(@ad< "20030917" @rlad< "20030917") and 43	US-PGPUB; USPAT	OR	OFF	2008/06/12 11:38
L45	0	( ((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) near2 (ohmic electorde wiring contact)).clm.	EPO; JPO; DERWENT	OR	OFF	2008/06/12 12:01
L46	995	( ((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) near2 (ohmic electorde wiring contact))	EPO; JPO; DERWENT	OR	OFF	2008/06/12 12:02
L47	0	46 and (gallium near3 nitride gan algan nitride \$1based gan).clm.	EPO; JPO; DERWENT	OR	ON	2008/06/12 12:03
L48	9	46 and (gallium near3 nitride gan algan nitride \$1based gan)	EPO; JPO; DERWENT	OR	ON	2008/06/12 12:03
L49	6	"2001077413" "2000286448"	EPO; JPO; DERWENT	OR	ON	2008/06/12 12:05
L50	1	"20020056836" and "20a"	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2008/06/12 12:08

L51	6	buffer\$4 near3 (p\$1clad\$3 P \$1gan p\$1region p\$1layer p adj clad\$3 P adj gan p adj region p adj layer) and (gallium near3 nitride gan algan nitride\$1based gan)	EPO; JPO; DERWENT	OR	ON	2008/06/12 12:11
L52	3	(anti-ESD anti adj ESD) and (gallium near3 nitride gan algan nitride\$1based gan)	EPO; JPO; DERWENT	OR	ON	2008/06/12 12:51
L53	5	(anti-ESD anti adj ESD) and (gallium near3 nitride gan algan nitride\$1based gan)	US-PGPUB; USPAT	OR	ON	2008/06/12 12:53
L54	5	(anti\$1ESD anti adj ESD) and (gallium near3 nitride gan algan nitride\$1based gan)	US-PGPUB; USPAT	OR	ON	2008/06/12 12:54
L55	43	((LIANG-WEN) near2 (WU)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 12:59
L56	27	((RU-CHIN) near2 (TU)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 12:59
L57	28	((CHENG-TSANG) near2 (YU)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 12:59
L58	27	((TZU-CHI) near2 (WEN)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 12:59
L59	72	((FEN-REN) near2 (CHIEN)). INV.	US-PGPUB; USPAT	OR	OFF	2008/06/12 13:00
L60	17	(@ad< "20030917" @rlad< "20030917") and (55 56 57 58 59)	US-PGPUB; USPAT	OR	OFF	2008/06/12 13:00
L61	0	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non-doped non adj doped not-doped non adj doped i-type adj semiconductor intrinsic)) and 60	EPO; JPO; DERWENT	OR	OFF	2008/06/12 13:01
L62	0	(anti\$1ESD anti adj ESD) and 60	US-PGPUB; USPAT	OR	ON	2008/06/12 13:01
L63	2076	257/E33.005 257/E33.028 257/E33.064.ccls.	US-PGPUB; USPAT	OR	OFF	2008/06/12 13:13

L64	9	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) and 60	US-PGPUB; USPAT	OR	OFF	2008/06/12 13:13
L65	410	257/E33.005 257/E33.028  257/E33.064.ccls.	EPO; JPO	OR	OFF	2008/06/12 13:31
L66	27	((itype i adj type non \$1intentional\$4 non adj intentional\$4 not \$1intentional\$4 not adj intentional\$4 intentional\$4 natural\$4 undop\$4)(non- doped non adj doped not- doped non adj doped i-type adj semiconductor intrinsic)) and 65	EPO; JPO; DERWENT	OR	OFF	2008/06/12 13:31
L67	13	66 and (gallium near3 nitride gan algan nitride \$1based gan)	EPO; JPO; DERWENT	OR	ON	2008/06/12 13:32
L68	5907	(257/103 257/744 257/745  257/98.ccls. 438/25 438/27. ccls.)	US-PGPUB; USPAT	OR	ON	2008/06/12 13:38
L69	3892	(@ad<"20030917" @rlad<"20030917") and 68	US-PGPUB; USPAT	OR	OFF	2008/06/12 13:38
L70	73	(@pd>"20071123") and 69	US-PGPUB; USPAT	OR	OFF	2008/06/12 13:41

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